

Data Sheet January 2000 File Number 2878.3

15A, 1000V Ultrafast Diode

The RURP15100 is an ultrafast diode with soft recovery characteristics (t_{rr} < 100ns). It has a low forward voltage drop and is of silicon nitride passivated, ion-implanted, epitaxial construction.

This device is intended for use as a freewheel/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor.

Formerly developmental type TA09906.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURP15100	TO-220AC	RURP15100

NOTE: When ordering, use the entire part number.

Symbol



Features

•	Ultrafast with Soft Recovery	<100ns
•	Operating Temperature	.175 ⁰ C
•	Reverse Voltage	.1000V

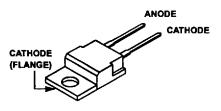
- · Avalanche Energy Rated
- · Planar Construction

Applications

- · Switching Power Supply
- · Power Switching Circuits
- · General Purpose

Packaging

JEDEC TO-220AC



Absolute Maximum Ratings T _C = 25°C, Unless Otherwise Specified		
	RURP15100	UNITS
Peak Repetitive Reverse VoltageVRRM	1000	V
Working Peak Reverse Voltage	1000	V
DC Blocking Voltage	1000	٧
Average Rectified Forward Current I _{F(AV)} (T _C = 142 ^o C)	15	Α
Repetitive Peak Surge CurrentI _{FRM} (Square Wave 20kHz)	30	Α
Nonrepetitive Peak Surge Current	200	Α
Maximum Power Dissipation	100	w
Avalanche Energy (See Figures 7 and 8)	20	mJ
Operating and Storage Temperature	-65 to 175	οС

RURP15100

Electrical Specifications T_C = 25°C, Unless Otherwise Specified.

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 15A	-	-	1.8	٧
	I _F = 15A, T _C = 150 ^o C	-	-	1.5	٧
l _R	V _R = 1000V	-	-	100	μА
	V _R = 1000V, T _C = 150°C	-	-	500	μА
t _{rr}	I _F = 1A, dI _F /dt = 100A/μs	-	-	100	ns
	I _F = 15A, dI _F /dt = 100A/μs	-	-	125	ns
t _a	I _F = 15A, dI _F /dt = 100A/μs	-	75	-	ns
t _b	I _F = 15A, dI _F /dt = 100A/μs	-	40	-	ns
R _{BJC}		-	-	1.5	°C/W

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300μs, D = 2%).

IR = Instantaneous reverse current.

 $t_{\rm rr}$ = Reverse recovery time at dI_F/dt = 100A/ μ s (See Figure 6), summation of t_a + t_b .

 t_a = Time to reach peak reverse current at dI_F/dt = 100A/ μ s (See Figure 6).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

Typical Performance Curves

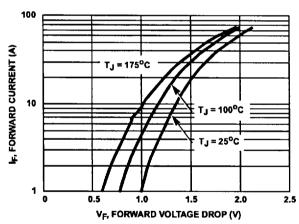


FIGURE 1. FORWARD CURRENT VS FORWARD VOLTAGE

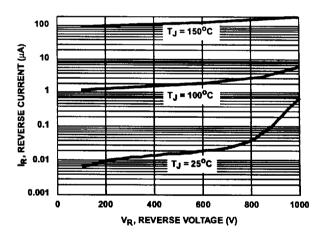


FIGURE 2. REVERSE CURRENT VS REVERSE VOLTAGE

Typical Performance Curves (Continued)

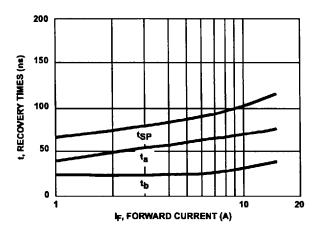


FIGURE 3. t_{rp} t_a AND t_b CURVES vs FORWARD CURRENT

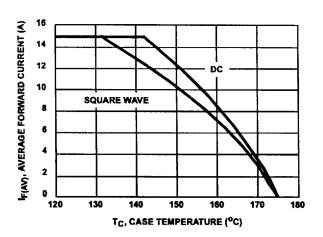


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

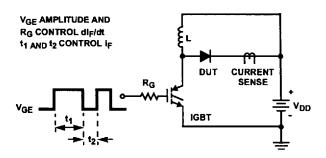


FIGURE 5. 4, TEST CIRCUIT

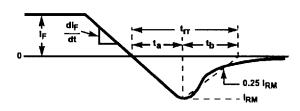


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

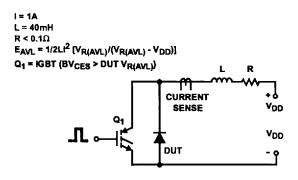


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

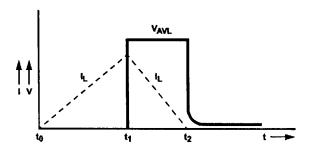


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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